2STA1962

High power PNP epitaxial planar bipolar transistor

Features

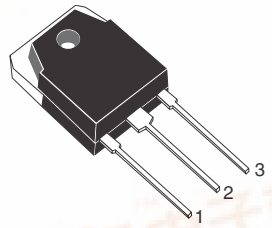
- High breakdown voltage V_{CEO} = -230 V
- Complementary to 2STC5242
- Fast-switching speed
- Typical f_T = 30 MHz

Application

- Audio power amplifier

Description

This device is a PNP transistor manufactured using new BiT-LA (Bipolar Transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.



TO-3P

Figure 1. Internal schematic diagram

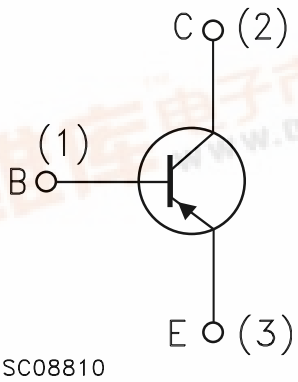


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA1962	2STA1962	TO-3P	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage (I_E = 0)	-230	V
V_{CEO}	Collector-emitter voltage (I_B = 0)	-230	V
V_{EBO}	Emitter-base voltage (I_C = 0)	-5	V
I_C	Collector current	-15	A
I_{CM}	Collector peak current	-30	A
P_{tot}	Total dissipation at T_C = 25 °C	150	W
T_{stg}	Storage temperature	-55 to 150	°C
T_J	Operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJ\text{-}case}$	Thermal resistance junction-case Max	0.83	°C/W

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current (I_E = 0)	V_{CB} = -230 V			-5	µA
I_{EBO}	Emitter cut-off current (I_C = 0)	V_{EB} = -5 V			-5	µA
$V_{(BR)CEO}$ (1)	Collector-emitter breakdown voltage (I_B = 0)	I_C = -50 mA	-230			V
$V_{(BR)CBO}$	Collector-base breakdown voltage (I_E = 0)	I_C = -100 µA	-230			V
$V_{(BR)EBO}$ (1)	Emitter-base breakdown voltage (I_C = 0)	I_E = -1 mA	-5			V
$V_{CE(sat)}$ (1)	Collector-emitter saturation voltage	I_C = -8 A I_B = -800 mA			-3	V
V_{BE}	Base-emitter voltage	I_C = -7 A V_{CE} = -5 V			-1.5	V
h_{FE}	DC current gain	I_C = -1 A V_{CE} = -5 V I_C = -7 A V_{CE} = -5 V	80 35		160	
t_{on} t_s t_f	Resistive load Turn-on time Storage time Fall time	V_{CC} = -60 V I_C = -5 A I_{B1}= -I_{B2} = -0.5 A		0.24 1.2 0.21		µs µs µs
f_T	Transition frequency	I_C = -1 A V_{CE} = -5 V		30		MHz
C_{CBO}	Collector-base capacitance (I_E = 0)	V_{CB} = -10 V f = 1 MHz		150		pF

1. Pulsed: pulse duration = 300 µs, duty cycle ≤ 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

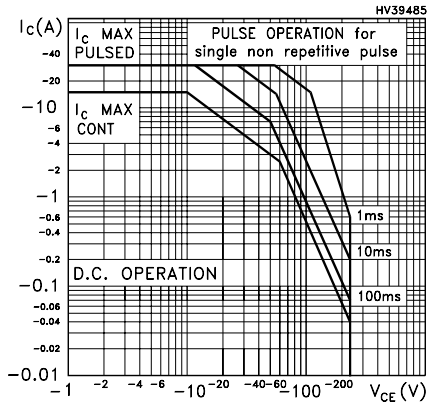


Figure 3. Derating curve

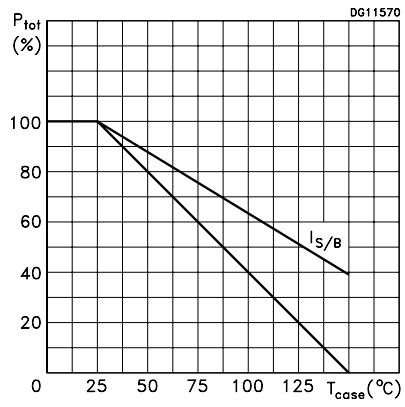


Figure 4. Output characteristics

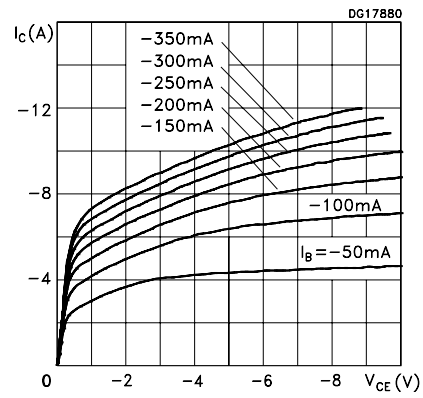


Figure 5. DC current gain

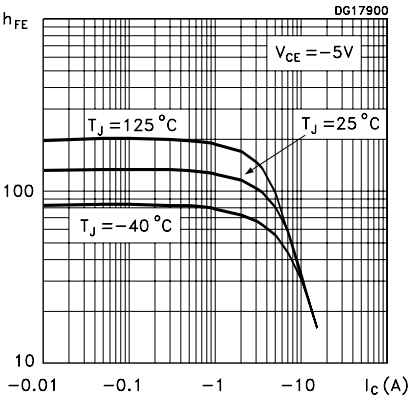


Figure 6. Collector-emitter saturation voltage

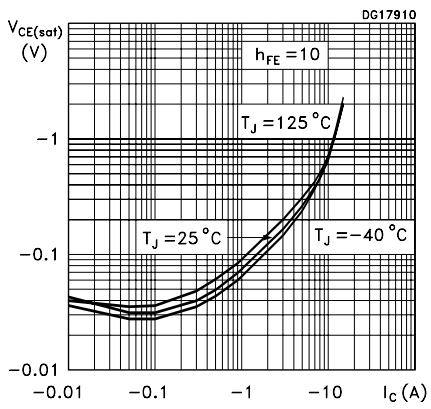
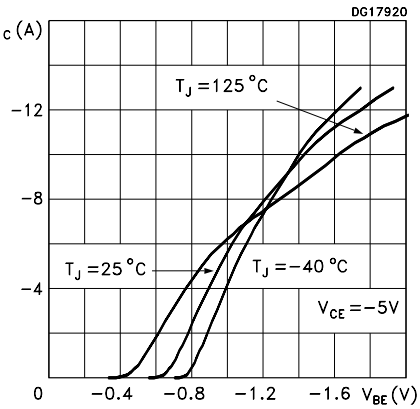
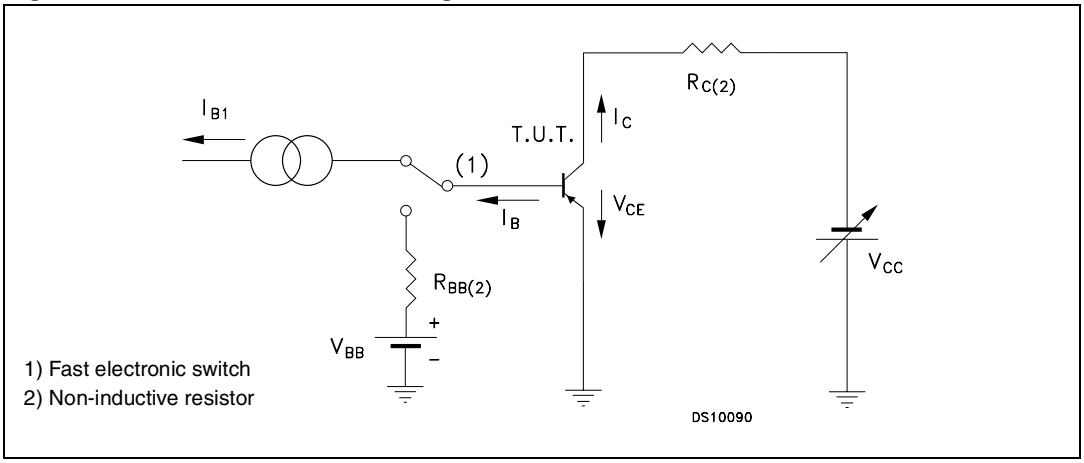


Figure 7. Collector current vs base-emitter voltage



2.2 Test circuit

Figure 8. Resistive load switching test circuit

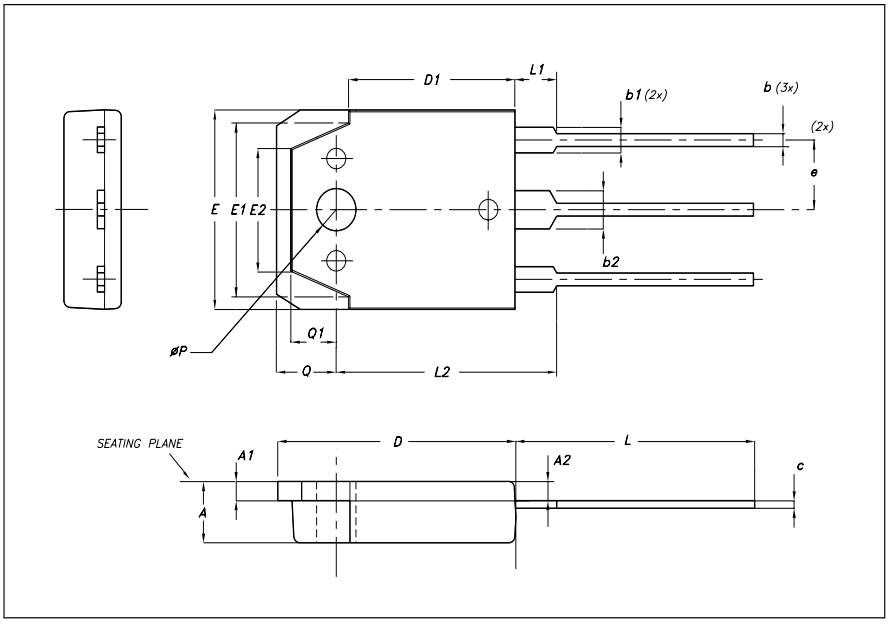


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

TO-3P Mechanical data

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
P	3.10		3.30
Q		5	
Q1		3.80	



4 Revision history

Table 5. Document revision history

Date	Revision	Changes
28-Sep-2007	1	Initial release.
12-Dec-2007	2	Document promoted from preliminary data to datasheet.
15-Jul-2008	3	Updated total power dissipation and relevant thermal resistance junction-case value.

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